

# Low-Temperature Sintering and Microwave Dielectric Properties of $\text{Li}_2\text{O}-3\text{ZnO}-5\text{TiO}_2$ Ceramics Doped with $\text{B}_2\text{O}_3$

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## Abstract

Phase composition, crystal structure as well as microwave dielectric properties of  $\text{Li}_2\text{O}-3\text{ZnO}-5\text{TiO}_2$  ceramics (LZT135, for short) with the addition of  $\text{B}_2\text{O}_3$  and  $\text{TiO}_2$  were investigated. X-ray diffraction (XRD) and energy-dispersive spectroscopy (EDS) results revealed that the samples with added  $\text{B}_2\text{O}_3$  and sintered at  $900^\circ\text{C}$  had formed solid solutions with a similar crystal structure to  $\text{Zn}_2\text{Ti}_3\text{O}_8$ . When 0.25 wt%  $\text{B}_2\text{O}_3$  was added, LZT135 ceramics could be densified at about  $900^\circ\text{C}$ , while the negative  $\tau_f$  value of about  $-31.5$  ppm/K restricted its applications.  $\text{TiO}_2$  was added for further adjustment of the  $\tau_f$  value of LZT135 ceramics. Finally, with the addition of 0.25 wt%  $\text{B}_2\text{O}_3$  and 9 wt%  $\text{TiO}_2$ , near zero  $\tau_f$  values of about  $-0.5$  ppm/K can be achieved for LZT135 ceramics, and at the same time, high Qf values of about 48 300 GHz are attractive for low-temperature co-firing ceramics technology.

*Keywords:* Microwave dielectric properties, LTCC,  $\text{Li}_2\text{O}-3\text{ZnO}-5\text{TiO}_2$

## I. Introduction

Low-temperature co-fired ceramic (LTCC, for short) technologies are widely used in RF wireless communication, electronic packaging, automotive electronics, radar, and space navigation, etc. Since silver is usually used as the inner circuit patterns electrode for LTCC technologies, the sintering temperatures of these ceramics need to be lower than the melting point of silver, ordinarily  $900^\circ\text{C}$  or even lower<sup>1</sup>. Lots of ceramic materials with low sintering temperature have been developed to meet the demands of LTCC technologies. Zn-containing compounds and Li-containing compounds, such as  $\text{Li}_2\text{O}-\text{Nb}_2\text{O}_5-\text{TiO}_2$ ,  $\text{Zn}-\text{TiO}_3$ ,  $\text{Zn}_2\text{SiO}_4$ , and  $\text{ZnNb}_2\text{O}_6$ , have attracted much attention especially owing to their relatively low sintering temperatures, as well as low dielectric loss at microwave frequency<sup>2-9</sup>.

Compared with other LTCC materials,  $\text{Li}_2\text{ATi}_3\text{O}_8$  (A=Mg, Zn) ceramics with a sintering temperature of about  $1075^\circ\text{C}$  and a high Qf value of 72 000 GHz, as reported by S. George and M.T. Sebastian in 2010<sup>10,11</sup>, are very attractive for LTCC applications. Another system,  $\text{ZnLi}_{2/3}\text{Ti}_{4/3}\text{O}_4$  ( $\text{Li}_2\text{O}-3\text{ZnO}-4\text{TiO}_2$ ) ceramic with a higher Qf value of 106 700 GHz was reported by Zhou<sup>12</sup>, however, its sintering temperature of  $1075^\circ\text{C}$  and large negative  $\tau_f$  value of  $-48$  ppm/K are still not suitable for most LTCC applications. A solid solution of  $\text{Li}_2\text{O}-3\text{ZnO}-5\text{TiO}_2$  (LZT135, for short) was reported in 2018<sup>13</sup>. Doping with  $\text{V}_2\text{O}_5$  reduced the sintering temperature of LZT135 to near  $900^\circ\text{C}$ , combined doping with  $\text{TiO}_2$  corrected the negative  $\tau_f$  value to near zero, however, the

toxicity of  $\text{V}_2\text{O}_5$  still hampered application.  $\text{B}_2\text{O}_3$  is usually used as the sintering aid because of its low melting point of about  $450^\circ\text{C}$ <sup>14-16</sup>, so  $\text{B}_2\text{O}_3$  replaces  $\text{V}_2\text{O}_5$  in this research for lower the sintering temperatures of the promising LZT135 ceramics system.

## II. Experimental Procedure

$\text{Li}_2\text{O}-3\text{ZnO}-5\text{TiO}_2$  ceramics were synthesized with the conventional solid-state reaction method.  $\text{Li}_2\text{CO}_3$ ,  $\text{TiO}_2$ ,  $\text{ZnO}$ , and  $\text{B}_2\text{O}_3$  powder (reagent grade, over 99 wt%) were mixed and milled using deionized water and zirconia balls as milling media. After drying, the mixtures were calcined at  $900^\circ\text{C}$  for 3 h. Different amounts of  $\text{B}_2\text{O}_3$  and  $\text{TiO}_2$  were then added and the mixture was remilled and dried. The resulting powder was pressed into disks under a pressure of 100 MPa with a size of 14 mm in diameter and 6 ~ 8 mm in thickness. Finally, samples were sintered at  $875-925^\circ\text{C}$  for 3 h in an air atmosphere.

The bulk density of the sintered samples was measured with the Archimedes' method. The microstructure of the specimens was examined by means of X-ray diffraction (XRD, model Shimadzu XRD-7000) and a scanning electron microscope (SEM, model JEOL JSM-64). Element composition analysis was performed using an energy-dispersive spectrometer (EDS, model Oxford X-max N50). The microwave dielectric properties were measured with Hakki and Coleman's method<sup>17,18</sup>. The  $\tau_f$  value was also measured with the same method in the temperature range of  $25-75^\circ\text{C}$ .

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### III. Results and Discussion

Fig. 1 shows the XRD patterns of sintered LZT135 ceramics doped with different amounts of  $B_2O_3$ , all the samples were sintered at  $900\text{ }^\circ\text{C}$ . XRD results showed that the sintered LZT135 ceramics formed a cubic structure similar to  $Zn_2Ti_3O_8$  (JCPDS087–1781) with lattice parameters of  $a = 8.382\text{ \AA}$ ,  $V = 588.9\text{ \AA}^3$ . The  $2\theta$  positions of all of the peaks closely match the  $(1-x)Li_2Zn_3Ti_4O_{12-x}TiO_2$  (where  $0.2 \leq x \leq 0.4$ ) ceramics phase previously reported by Liu<sup>19</sup>. Therefore, the  $B_2O_3$  doping does not strongly influence the phase composition of LZT135.

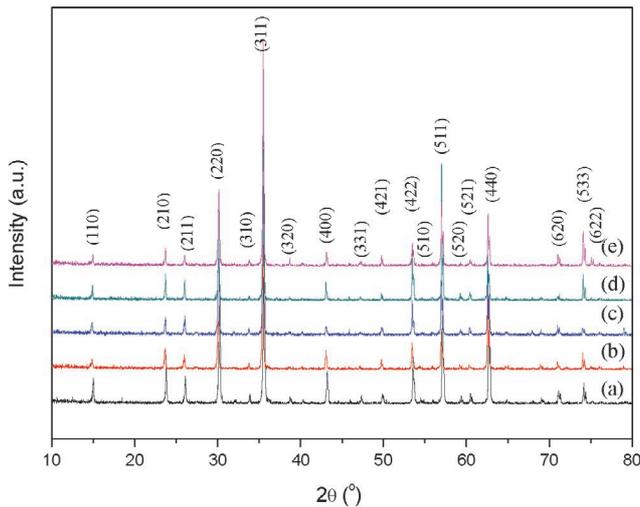


Fig. 1: XRD patterns of the sintered LZT135 ceramics doped with different amounts of  $B_2O_3$  and sintered at  $900\text{ }^\circ\text{C}$ , where (a) 0 wt% (b) 0.25 wt%, (c) 0.5 wt%, (d) 0.75 wt% and (e) 1 wt%.

Fig. 2 shows the bulk densities of LZT135 ceramics sintered at different temperatures and different  $B_2O_3$  doping levels. It is clear that  $B_2O_3$  increases the density of LZT135 ceramics in the temperature range of  $875\text{--}925\text{ }^\circ\text{C}$ . This can be explained by the low melting point of  $B_2O_3$  at  $450\text{ }^\circ\text{C}$ , which forms liquid phases that can enhance the grain rearrangement and densification of LZT135 ceramics. LZT135 ceramic reaches a density of  $4.07\text{ g/cm}^3$  with 0.25 wt%  $B_2O_3$  addition and after sintering at  $900\text{ }^\circ\text{C}$ . Doping beyond these levels did not improve densification.

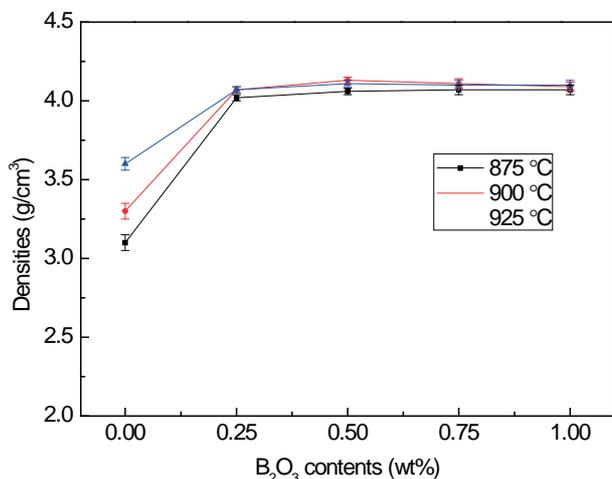


Fig. 2: Densities of LZT135 ceramics as a function of the  $B_2O_3$  addition content and sintering temperatures.

The SEM micrographs in Fig. 3 show sintered LZT135 with different levels of  $B_2O_3$  doping. When  $B_2O_3$  was added, LZT135 exhibited two types of grains: bigger grains of about  $40\text{ }\mu\text{m}$  (marked A), and smaller grains about  $1\text{ }\mu\text{m}$  (marked B). EDS results, in Fig. 4, showed that these two types of grains mainly contained Zn, Ti, and O elements, with nearly the same atomic ratio of Zn : Ti = 3 : 5. According to the XRD analysis results and EDS analysis, with the addition of  $B_2O_3$  and sintering at about  $900\text{ }^\circ\text{C}$ , LZT135 ceramics can form solid solutions.

The microwave dielectric properties of  $B_2O_3$ -doped LZT135 are shown in Fig. 5. For samples doped with 0.25 wt%  $B_2O_3$  and sintered at  $900\text{ }^\circ\text{C}$ , the  $\epsilon_r$  of LZT135 reaches a relatively high value of 20.5, while again further additions of  $B_2O_3$  have almost no influence on  $\epsilon_r$  values as found earlier for density values. With increasing amounts of  $B_2O_3$ , the Qf values of LZT135 decreased markedly regardless of sintering temperatures, which could be explained by high dielectric losses coming from the liquid phase. Doping with  $B_2O_3$  does not impact the  $\tau_f$  values of LZT135 with 0.25 wt%  $B_2O_3$  exhibiting  $-30\text{ ppm/K}$ , which is unacceptable in application.  $TiO_2$  has an unusually high positive  $\tau_f$  value of  $+465\text{ ppm/K}$ , and therefore,  $TiO_2$  doping was used to significantly reduce the negative  $\tau_f$  values of some ceramics<sup>20–22</sup>.

The XRD patterns for different  $TiO_2$  levels are shown in Fig. 6. The major crystal phase of all the samples is LZT135 solid solution as mentioned above, however, a secondary phase, rutile  $TiO_2$ , was detected. Fig. 7 illustrates the microstructure of the as-sintered surface of LZT135 ceramics doped with  $B_2O_3$  and  $TiO_2$ , which is still well-densified with low porosity. The grain size of LZT135 is smaller and more uniform with increased  $TiO_2$ , and this might stem from the high sintering temperature of  $TiO_2$  ceramic (above  $1300\text{ }^\circ\text{C}$ ).

Fig. 8 shows the improved sintered densities and microwave dielectric properties of LZT135 as a function of  $TiO_2$  doping. The sintered densities and dielectric constants of LZT135 ceramics increased with the amounts of  $TiO_2$  added. These increases mostly occur owing to the presence of the  $TiO_2$  phase, which has a higher sintered density and dielectric constant. The Qf values of the LZT135 increased slightly with  $TiO_2$  doping and reached a maximum value of about  $50\text{ }000\text{ GHz}$  at 5 wt%  $TiO_2$ . Dielectric loss in ceramics can be divided into intrinsic loss and extrinsic loss. Intrinsic loss is mainly determined by the crystal structure, while extrinsic loss is determined by factors such as, density, grain size, porosity, and second phases<sup>23</sup>.  $TiO_2$  doping at less than 5 wt% increased density and decreased grain size to effect higher Qf values. This is balanced by the continued increase of rutile  $TiO_2$  phase, which has a lower Qf value, which affects the LZT135 Qf overall. Within the sintering temperature range  $875\text{--}925\text{ }^\circ\text{C}$ ,  $\tau_f$  values of LZT135 ceramics shifted from negative to positive values with the doping of  $TiO_2$  because of the rutile phase, effecting a near zero  $\tau_f$  value. The optimal doping levels of 0.25 wt%  $B_2O_3$  and 9 wt%  $TiO_2$  in LZT135 sintered at  $900\text{ }^\circ\text{C}$  led to excellent dielectric properties of  $\epsilon_r = 24.9$ , Qf =  $48\text{ }300\text{ GHz}$  and  $\tau_f = -0.5\text{ ppm/K}$ .

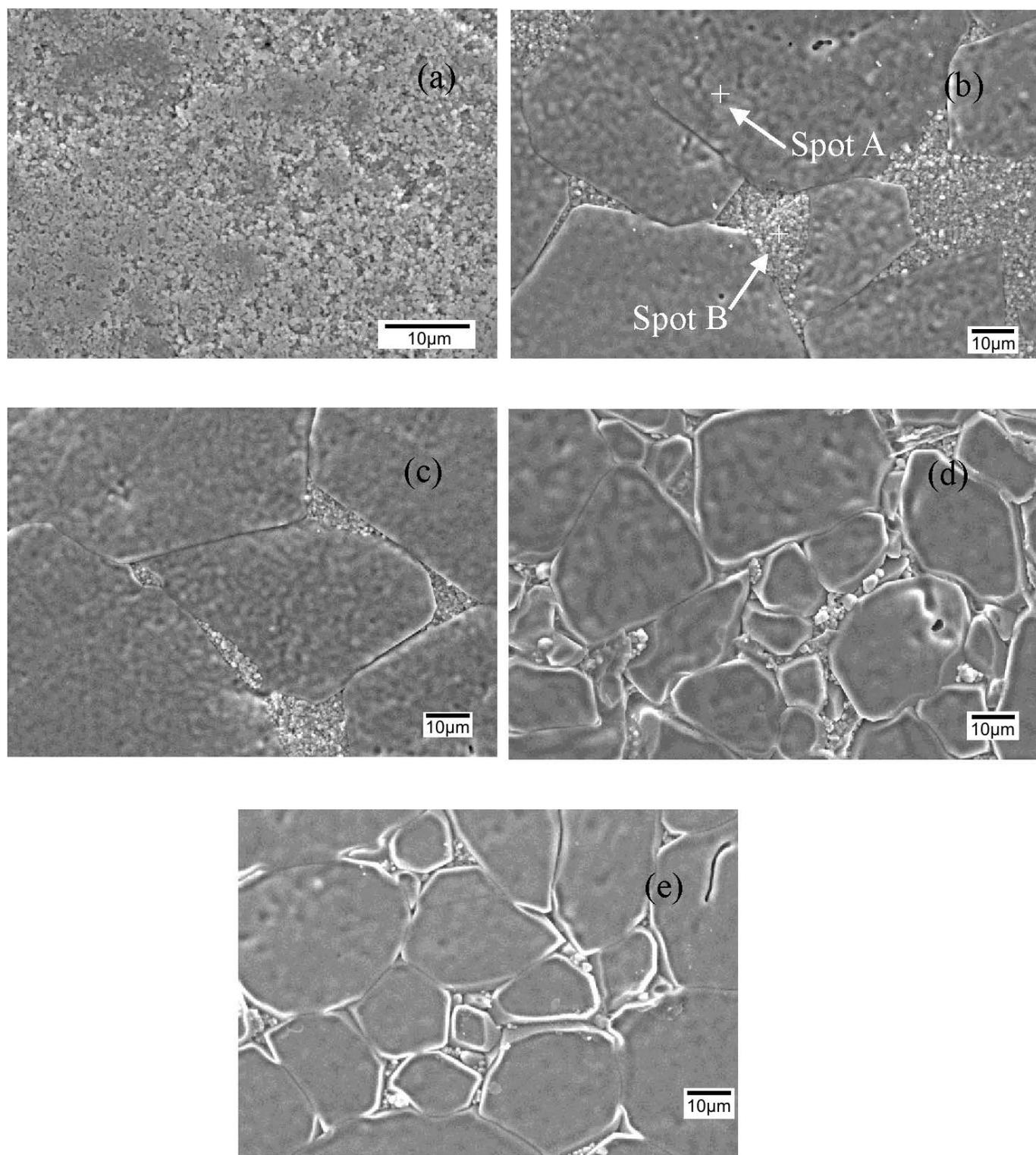


Fig. 3: SEM micrographs of LZT135 ceramics doped with different amounts of  $\text{B}_2\text{O}_3$  and sintered at  $900^\circ\text{C}$  for 3 h.

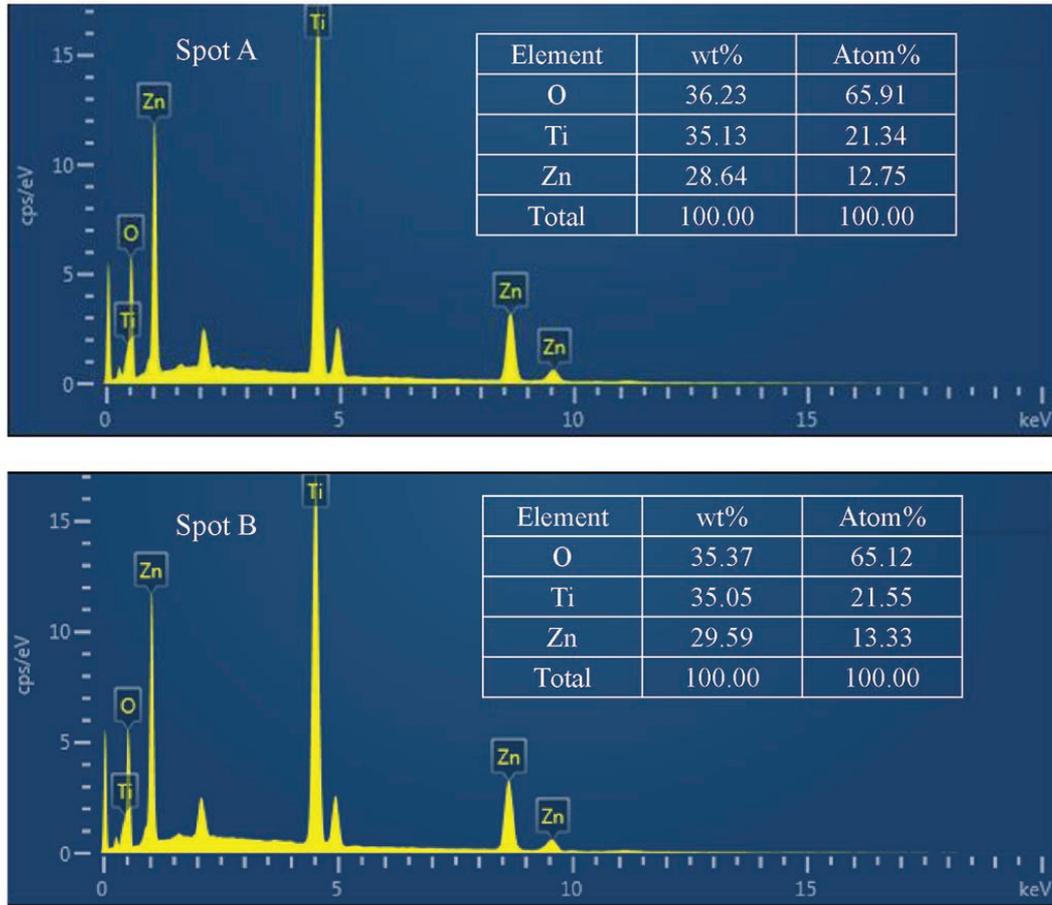


Fig. 4: EDS analysis of  $\text{Li}_2\text{ZnTi}_3\text{O}_8$  ceramic with 0.25 wt%  $\text{B}_2\text{O}_3$  added and sintered at 900 °C for 3 h.

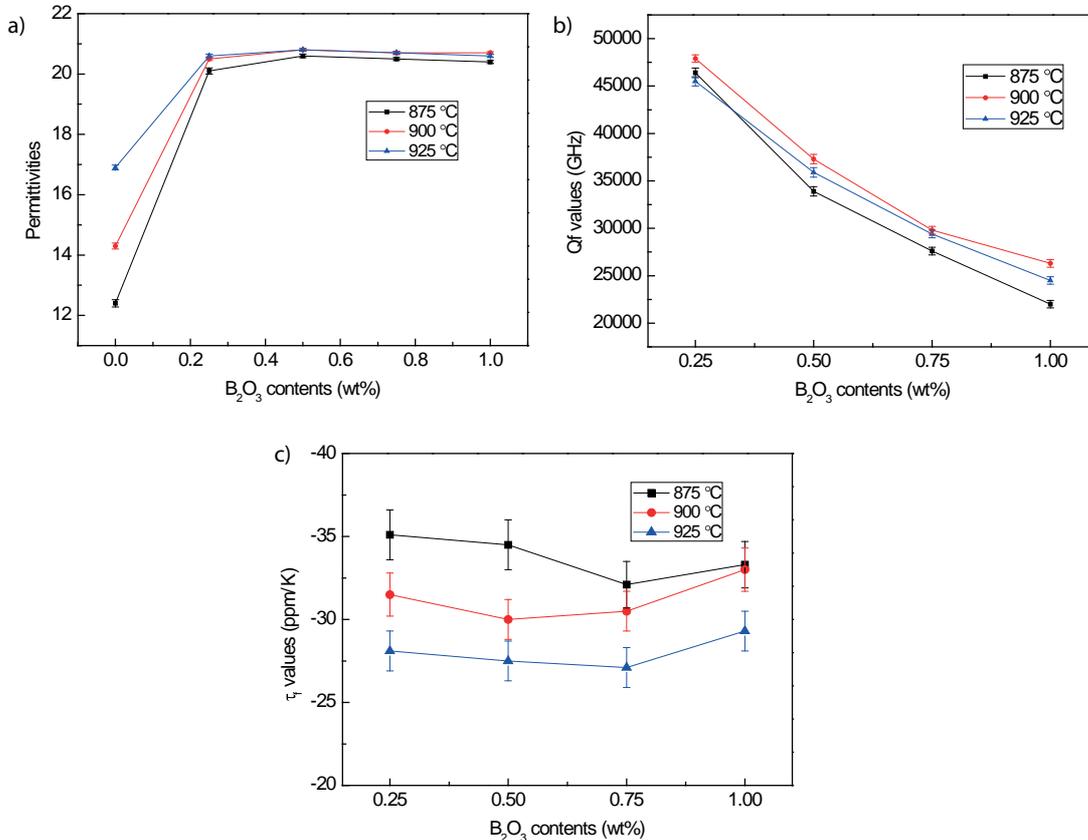
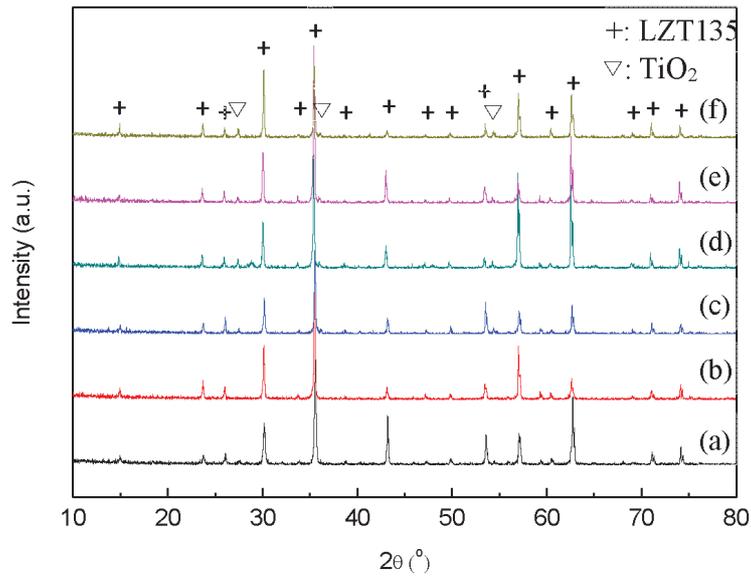
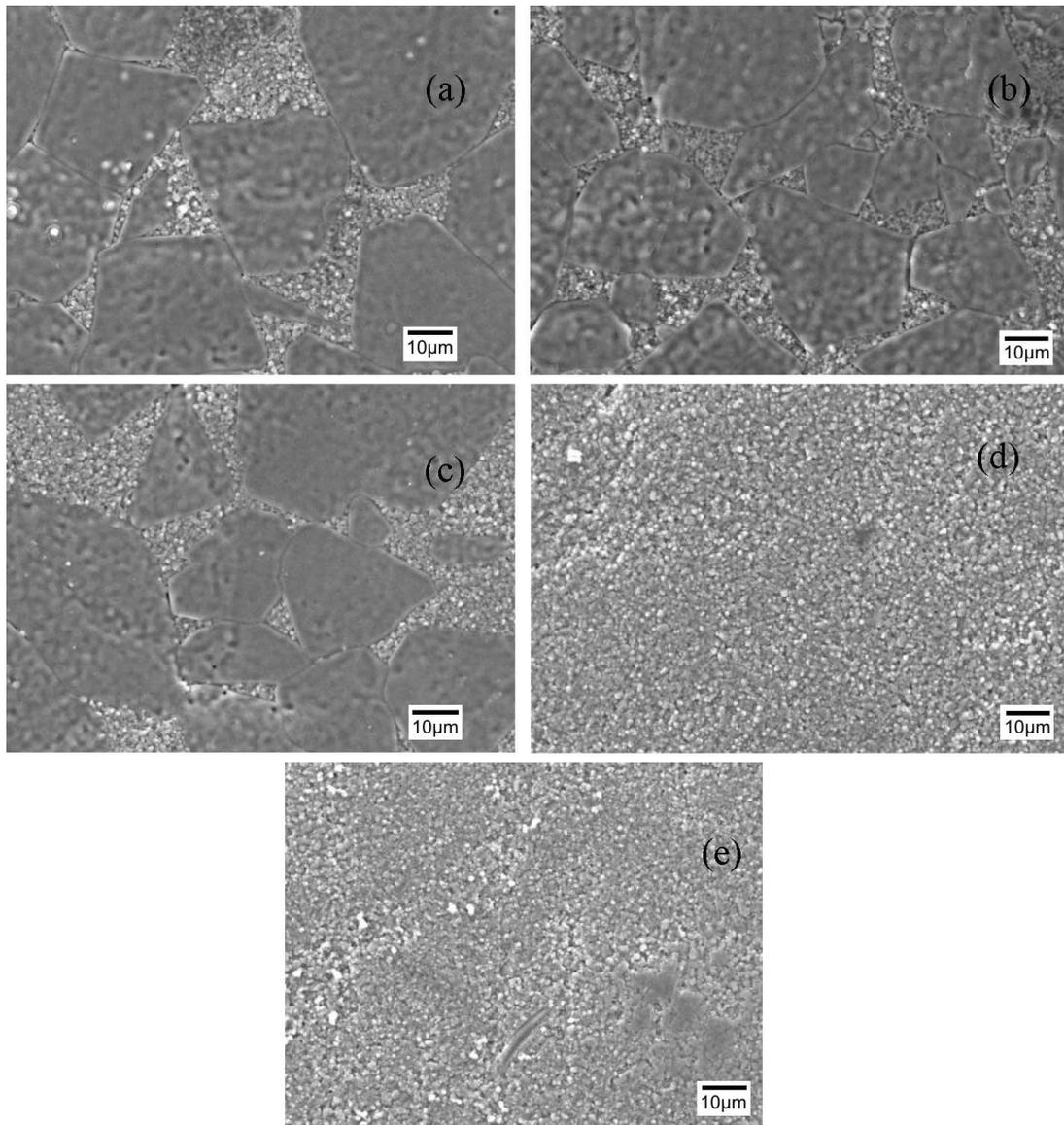


Fig. 5: Microwave dielectric properties of LZT135 ceramics as a function of the  $\text{B}_2\text{O}_3$  addition contents and sintering temperature; (a) Permittivities; (b) Qf values; (c)  $\tau_f$  values.



**Fig. 6:** XRD patterns of LZT135 ceramics doped with 0.25 wt%  $\text{B}_2\text{O}_3$  and different amounts of  $\text{TiO}_2$ , where (a) 0 wt%, (b) 2.5 wt%, (c) 5.0 wt%, (d) 7.5 wt%, (e) 9.0 wt% and (f) 10.0 wt%.



**Fig. 7:** SEM micrographs of LZT135 ceramics doped with 0.25 wt%  $\text{B}_2\text{O}_3$  and different amounts of  $\text{TiO}_2$ , where (a) 2.5 wt%, (b) 5.0 wt%, (c) 7.5 wt%, (d) 9.0 wt% and (e) 10.0 wt%.

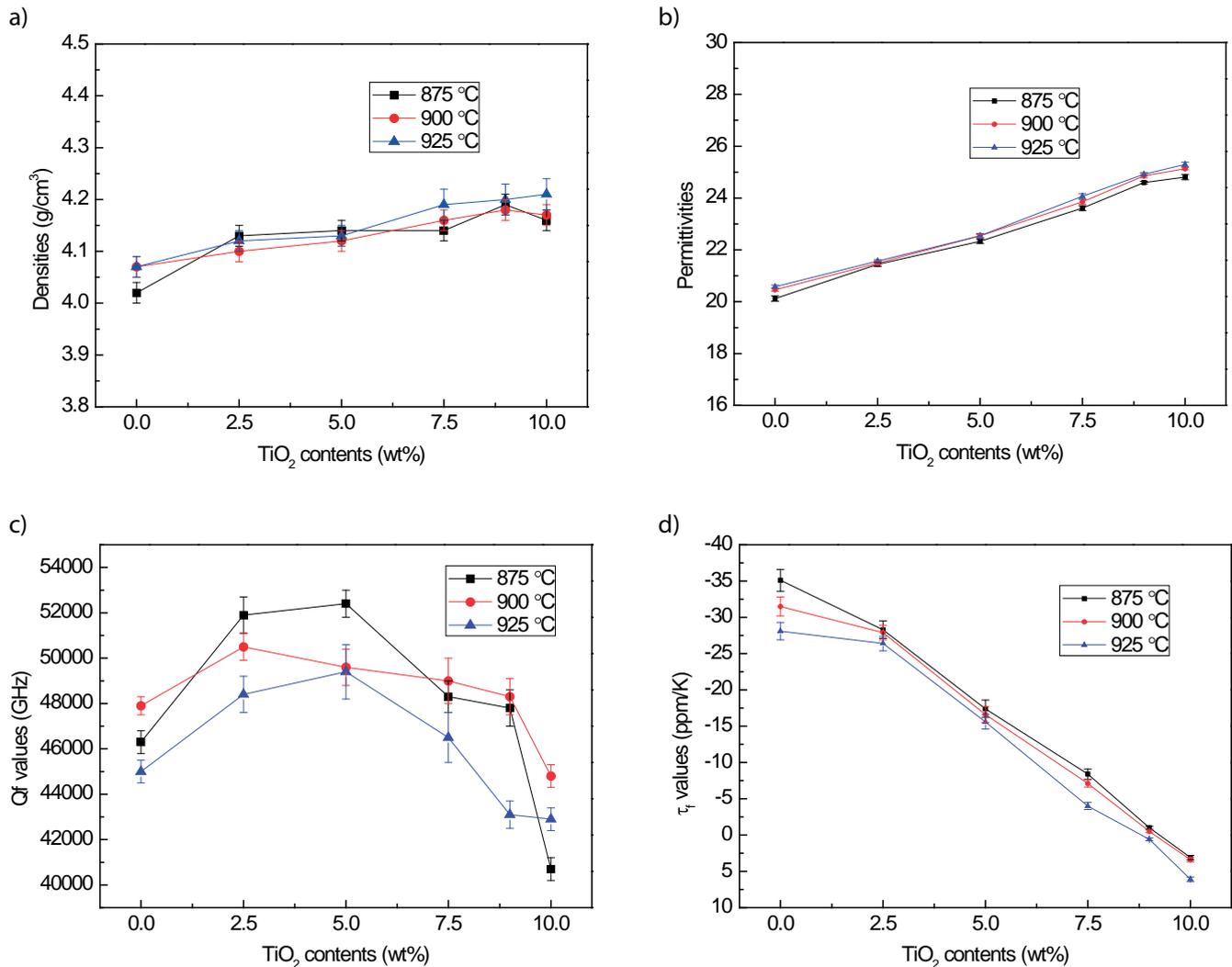


Fig. 8: Densities and microwave dielectric properties of LZT135 ceramics as a function of the TiO<sub>2</sub> addition contents and sintering temperature; (a) Sintered densities; (b) Permittivities; (c) Qf values; (d) τ<sub>f</sub> values.

#### IV. Conclusions

The addition of B<sub>2</sub>O<sub>3</sub> can effectively decrease the sintering temperature of LZT135 ceramics to about 900 °C. XRD and EDS results showed that the LZT135 ceramics formed a solid solution with a similar crystal structure to Zn<sub>2</sub>Ti<sub>3</sub>O<sub>8</sub>. When 0.25 wt% B<sub>2</sub>O<sub>3</sub> was added, dielectric properties of ε<sub>r</sub> = 20.5, Qf = 47 900 GHz and τ<sub>f</sub> = -31.5 ppm/K could be obtained. The addition of TiO<sub>2</sub> formed a secondary phase of rutile TiO<sub>2</sub> in LZT135 ceramics, and can thus adjust the τ<sub>f</sub> values for LZT135 ceramics. With the addition of 0.25 wt% B<sub>2</sub>O<sub>3</sub> and 9 wt% TiO<sub>2</sub>, LZT135 ceramics exhibited excellent microwave dielectric properties with ε<sub>r</sub> = 24.9, Qf = 48 300 GHz and τ<sub>f</sub> = -0.5 ppm/K when sintered at 900 °C.

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